

**REPLY UNDER 37 CFR 1.116
EXPEDITED PROCEDURE
TECHNOLOGY CENTER 2800**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:	William G. America	Conf. No.:	3775
Serial No.:	10/709,776	Art Unit:	2811
Filed:	5/27/2004	Dkt. #:	FIS920040083US1 (IBMF-0058)
Title:	SEMICONDUCTOR DEVICE FORMED BY IN-SITU MODIFICATION OF DIELECTRIC LAYER AND RELATED METHODS		
		Examiner:	Im, Junghwa M

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AFTER-FINAL AMENDMENT

Sir:

I. INTRODUCTORY COMMENTS

This paper is being filed in response to the Office Action dated May 17, 2007. Please amend the above-referenced patent application as follows: